

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A dielectric thin film including a bismuth layer compound having a c-axis oriented vertically with respect to a substrate surface, wherein:
the bismuth layer compound is composed of a thin film capacitance element composition, wherein: composition;
~~at the bismuth layer compound having a c-axis oriented vertically with respect to a substrate surface~~ is expressed by a composition formula of $(\text{Bi}_2\text{O}_2)^{2+} (\text{A}_{m-1} \text{B}_m \text{O}_{3m+1})^{2-}$ or $\text{Bi}_2\text{A}_{m-1} \text{B}_m \text{O}_{3m+3}$, ~~wherein wherein:~~
"m" is an even number,
"A" is at least one element selected from Na, K, Pb, Ba, Sr, Ca and Bi,
and
"B" is at least one element selected from Fe, Co, Cr, Ga, Ti, Nb, Ta, Sb, V, Mo and W; and

Bi in said bismuth layer compound is excessively included with respect to said composition formula of $(\text{Bi}_2\text{O}_2)^{2+} (\text{A}_{m-1} \text{B}_m \text{O}_{3m+1})^{2-}$ or $\text{Bi}_2\text{A}_{m-1} \text{B}_m \text{O}_{3m+3}$, and the excessive content of Bi is in a range of $0 < \text{Bi} < 0.5xm$ mol in terms of Bi.

2. (Currently Amended) The dielectric thin film capacitance element composition as set forth in claim 1, wherein the excessive content of Bi is in a range of $0.4 \leq \text{Bi} < 0.5xm$ mol in terms of Bi.

3. (Currently Amended) A dielectric thin film including a bismuth layer compound having a c-axis oriented vertically with respect to a substrate surface, wherein:
the bismuth layer compound is composed of a thin film capacitance element composition, wherein a composition;

~~_____ the bismuth layer compound having a c-axis oriented vertically with respect to a substrate surface~~ is expressed by a composition formula of $\text{SrBi}_4\text{Ti}_4\text{O}_{15}$; and

Bi in ~~said~~ the bismuth layer compound is excessively included with respect to said composition formula of $\text{SrBi}_4\text{Ti}_4\text{O}_{15}$, and the excessive content of Bi is in a range of $0 < \text{Bi} < 2.0 \times 10^{-2}$ mol in terms of Bi.

4. (Currently Amended) A dielectric thin film including a bismuth layer compound having a c-axis oriented vertically with respect to a substrate surface, wherein:

~~_____ the bismuth layer compound is composed of a thin film capacitance element composition, wherein a composition;~~

~~_____ the bismuth layer compound having a c-axis oriented vertically with respect to a substrate surface~~ is expressed by a composition formula of $\text{SrBi}_4\text{Ti}_4\text{O}_{15}$; and

Bi in ~~said~~ the bismuth layer compound is excessively included with respect to said composition formula of $\text{SrBi}_4\text{Ti}_4\text{O}_{15}$, and when the excessive content of Bi is expressed by a mole ratio (Bi/Ti) against Ti, Bi/Ti is in a range of $1 < \text{Bi/Ti} < 1.5$.

5. (Currently Amended) A dielectric thin film including a bismuth layer compound having a c-axis oriented vertically with respect to a substrate surface, wherein:

~~_____ the bismuth layer compound is composed of a thin film capacitance element composition, wherein composition;~~

~~_____ at~~ the bismuth layer compound ~~having a c-axis oriented vertically with respect to a substrate surface~~ is expressed by a composition formula of $\text{Sr}_x\text{Ca}_y\text{Ba}_z\text{Bi}_4\text{Ti}_4\text{O}_{16}$, $x+y+z=1$, $0 \leq x \leq 1$, $0 \leq y \leq 1$ and $0 \leq z \leq 1$; and

Bi in ~~said~~ the bismuth layer compound is excessively included with respect to said composition formula of $\text{Sr}_x\text{Ca}_y\text{Ba}_z\text{Bi}_4\text{Ti}_4\text{O}_{15}$, and when the excessive content of Bi is expressed by a mole ratio (Bi/Ti) against Ti, Bi/Ti is in a range of $1 < \text{Bi/Ti} < 1.5$.

6. (Currently Amended) The dielectric thin film ~~capacitance element~~ composition as set forth in claim 1, the thin film capacitance element composition ~~furthermore including a further comprising at least one~~ rare earth element ~~(at least one~~ selected from the group consisting of Sc, Y, La, Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb and ~~Lu~~) Lu.

7. (Currently Amended) The dielectric thin film ~~capacitance element~~ composition as set forth in claim 1, wherein a c-axis orientation degree of ~~said~~ the bismuth layer compound with respect to ~~said~~ the substrate surface is 80% or more.

8. (Currently Amended) The dielectric thin film ~~capacitance element~~ composition as set forth in claim 1, wherein leakage current density at electric field intensity of 50 kV/cm is 1×10^{-7} A/cm² or lower.

9. (Currently Amended) The dielectric thin film ~~capacitance element~~ composition as set forth in claim 1, wherein an average change rate of a capacitance against a temperature in a range of -55 to +150°C is ± 500 ppm/°C with the reference temperature of 25°C.

10. (Currently Amended) A thin film capacitance element, wherein a lower portion electrode, the dielectric thin film as set forth in claim 1, and an upper portion electrode are successively formed on a substrate, ~~wherein~~
~~_____ said dielectric film is composed of the thin film capacitance element composition as set forth in claim 1.~~

11. (Original) The thin film capacitance element as set forth in claim 10, wherein a thickness of said dielectric thin film is 1 to 1000 nm.

12. (Currently Amended) A thin film multilayer capacitor, wherein a plurality of the dielectric thin films as set forth in claim 1 and internal electrode thin films are alternately stacked on a substrate, ~~wherein~~

~~_____ said dielectric thin film is composed of the thin film capacitance element composition as set forth in claim 1.~~

13. (Original) The thin film multilayer capacitor as set forth in claim 12, wherein a thickness of said dielectric thin film is 1 to 1000 nm.

14-24. (Canceled)